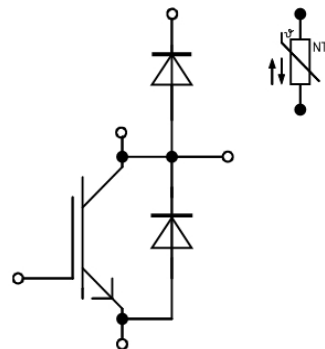
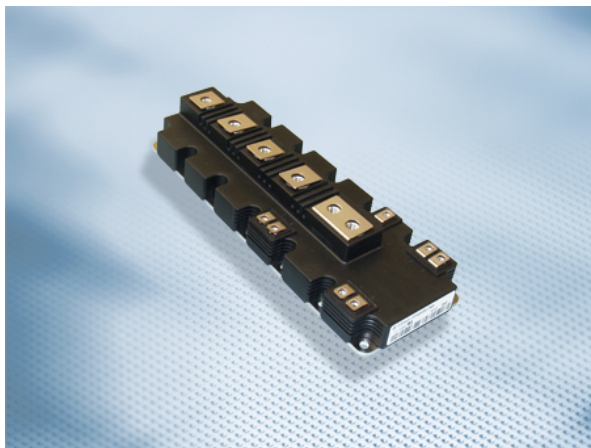


PrimePACK™3 Modul und NTC
PrimePACK™3 module and NTC

Vorläufige Daten / Preliminary Data



$V_{CES} = 1700V$
 $I_{C\ nom} = 1000A / I_{CRM} = 2000A$

Typische Anwendungen

- 3-Level-Applikationen
- Chopper-Anwendungen
- Hilfsumrichter
- Hochleistungsumrichter
- Motorantriebe
- Traktionsumrichter
- Windgeneratoren

Typical Applications

- 3-Level-Applications
- Chopper Applications
- Auxiliary Inverters
- High Power Converters
- Motor Drives
- Traction Drives
- Wind Turbines

Elektrische Eigenschaften

- Erweiterte Sperrschichttemperatur $T_{vj\ op}$
- Große DC-Festigkeit
- Hohe Stromdichte
- Niedrige Schaltverluste
- Niedriges V_{CEsat}
- $T_{vj\ op} = 150^{\circ}C$
- Verstärkte Diode für Rückspeisebetrieb

Electrical Features

- Extended Operation Temperature $T_{vj\ op}$
- High DC Stability
- High Current Density
- Low Switching Losses
- Low V_{CEsat}
- $T_{vj\ op} = 150^{\circ}C$
- Enlarged Diode for regenerative operation

Mechanische Eigenschaften

- Gehäuse mit CTI > 400
- Große Luft- und Kriechstrecken
- Hohe Last- und thermische Wechselfestigkeit
- Hohe Leistungsdichte

Mechanical Features

- Package with CTI > 400
- High Creepage and Clearance Distances
- High Power and Thermal Cycling Capability
- High Power Density

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

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**Vorläufige Daten
Preliminary Data**

**IGBT-Chopper / IGBT-Chopper
Höchstzulässige Werte / Maximum Rated Values**

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1700	V
Kollektor-Dauergleichstrom Continuous DC collector current	$T_C = 100^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$ I_C	1000 1390	A A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	2000	A
Gesamt-Verlustleistung Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	P_{tot}	6,25	kW
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

			min.	typ.	max.		
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 1000\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 1000\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 1000\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	2,00 2,35 2,45	2,45 2,80	V V V	
Gate-Schwellenspannung Gate threshold voltage	$I_C = 36,0\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,2	5,8	6,4	V
Gateladung Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	10,0			μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	1,8			Ω
Eingangskapazität Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	81,0			nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	2,60			nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 1700\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		5,0		mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		400		nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 1000\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 0,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,66 0,70 0,71			μs μs μs
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 1000\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 0,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,10 0,11 0,12			μs μs μs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 1000\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	1,15 1,30 1,35			μs μs μs
Fallzeit, induktive Last Fall time, inductive load	$I_C = 1000\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,25 0,48 0,56			μs μs μs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 1000\text{ A}, V_{CE} = 900\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 8900\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 0,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	260 365 415			mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 1000\text{ A}, V_{CE} = 900\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 2800\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 1,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	210 315 345			mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 1000\text{ V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	4000			A
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro IGBT / per IGBT		R_{thJC}		24,0		K/kW
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	10,0			K/kW
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{op}}$	-40	150		$^{\circ}\text{C}$

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